

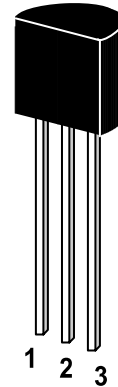
ST 2SA1268

PNP Silicon Epitaxial Planar Transistor

For high voltage applications.

The transistor is subdivided into two groups, G and L according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

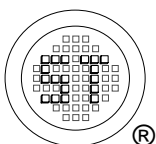


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	120	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	120	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	100	mA
Emitter Current	I_{E}	100	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_{j}	125	$^\circ\text{C}$
Storage Temperature Range	T_{s}	-55 to +125	$^\circ\text{C}$



SEMTECH ELECTRONICS LTD.

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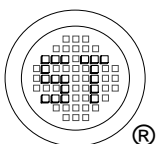


Dated : 07/12/2002

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Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE}=6\text{V}$, $-I_C=2\text{mA}$	Current Gain Group G	h_{FE}	200	-	400	-
	L	h_{FE}	350	-	700	-
Collector Emitter Breakdown Voltage at $-I_C=1\text{mA}$	$-V_{(BR)CEO}$	120	-	-	V	
Gain Bandwidth Product at $-V_{CE}=6\text{V}$, $-I_C=1\text{mA}$	f_T	-	100	-	MHz	
Noise Figure at $-V_{CE}=6\text{V}$, $-I_C=0.1\text{mA}$, $R_G=10\text{k}\Omega$, $f=10\text{Hz}$	NF	-	-	6	dB	
Output Capacitance at $-V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_{OB}	-	4	-	pF	
Base Emitter Voltage at $-V_{CE}=6\text{V}$, $-I_C=2\text{mA}$	$-V_{BE}$	-	0.65	-	V	
Collector Cutoff Current at $-V_{CB}=120\text{V}$	$-I_{CBO}$	-	-	0.1	μA	
Emitter Cutoff Current at $-V_{EB}=5\text{V}$	$-I_{EBO}$	-	-	0.1	μA	
Collector Saturation Voltage at $-I_C=10\text{mA}$, $-I_B=1\text{mA}$	$-V_{CE(sat)}$	-	-	0.3	V	



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